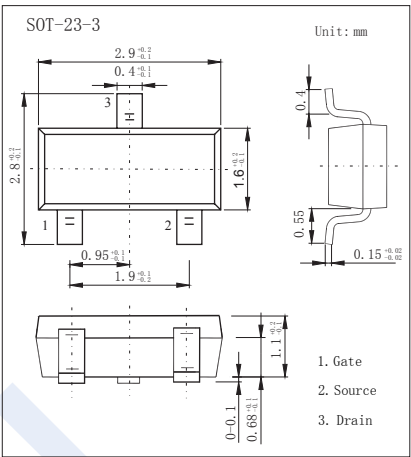
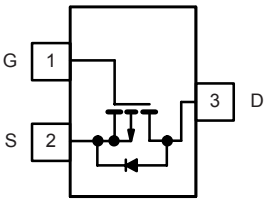


P-Channel MOSFET SI2343DS (KI2343DS)

■ Features

- $V_{DS} (V) \approx -30V$
- $I_D = -4 A (V_{GS} \approx -10V)$
- $R_{DS(ON)} < 53m \Omega (V_{GS} \approx -10V)$
- $R_{DS(ON)} < 86m \Omega (V_{GS} \approx -4.5V)$



■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	-30		V
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current	TA = 25 °C	ID	-4	-3.1	A
	TA = 70 °C		-3.2	-2.5	
Pulsed Drain Current		IDM	-15		
Power Dissipation	TA = 25 °C	PD	1.25	0.75	W
	TA = 70 °C		0.8	0.48	
Thermal Resistance.Junction- to-Ambient		RthJA	100	166	°C/W
Thermal Resistance.Junction- to-Foot		RthJF		50	
Junction Temperature		TJ	150		°C
Junction Storage Temperature Range		Tstg	-55 to 150		

P-Channel MOSFET

SI2343DS (KI2343DS)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _D =-24V, V _{GS} =0V			-1	μA
		V _D =-24V, V _{GS} =0V, T _J =55°C			-10	
Gate-Body leakage current	I _{GSS}	V _D =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _D =V _{GS} I _D =-250 μA	-1		-3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4A (Note.1)			53	mΩ
		V _{GS} =-4.5V, I _D =-3.1A (Note.1)			86	
On state drain current	I _{D(on)}	V _{GS} =-5V, V _D =-10V (Note.1)	-15			A
Forward Transconductance	g _{FS}	V _D =-5V, I _D =-4A (Note.1)		10		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _D =-15V, f=1MHz		540		pF
Output Capacitance	C _{oss}			131		
Reverse Transfer Capacitance	C _{rss}			105		
Total Gate Charge	Q _g	V _{GS} =-10V, V _D =-15V, I _D =-4A		14	21	nC
Gate Source Charge	Q _{gs}			1.9		
Gate Drain Charge	Q _{gd}			3.7		
Turn-On DelayTime	t _{d(on)}	V _{DD} = -15 V, R _L = 15 Ω I _D = -1A, V _{GEN} = -10 V R _G = 6 Ω		10	15	ns
Turn-On Rise Time	t _r			15	25	
Turn-Off DelayTime	t _{d(off)}			31	50	
Turn-Off Fall Time	t _f			20	30	
Maximum Body-Diode Continuous Current	I _S				-1	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1.2	V

Note.1: Pulse test: PW ≤ 300 μs, duty cycle ≤ 2 %.

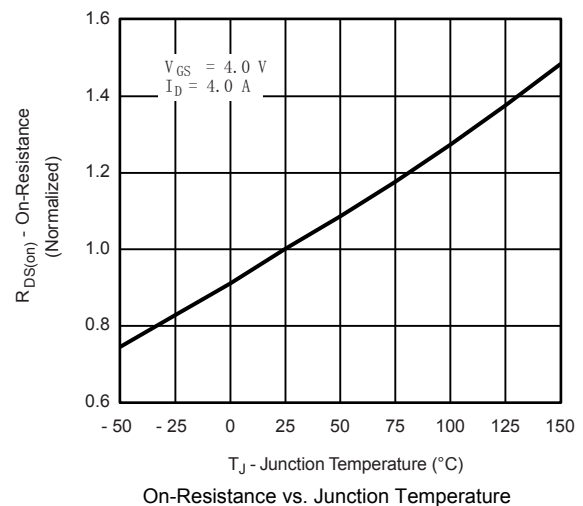
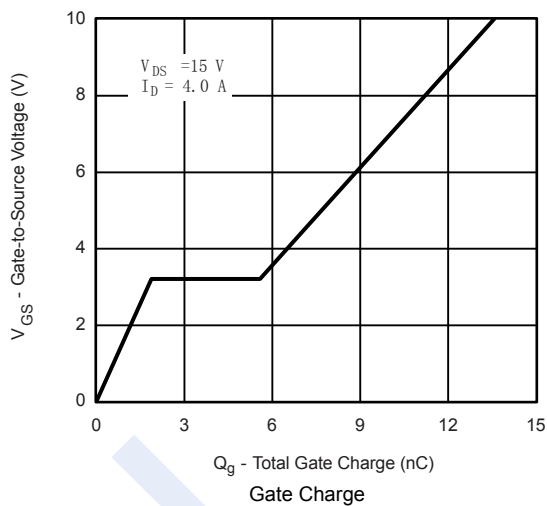
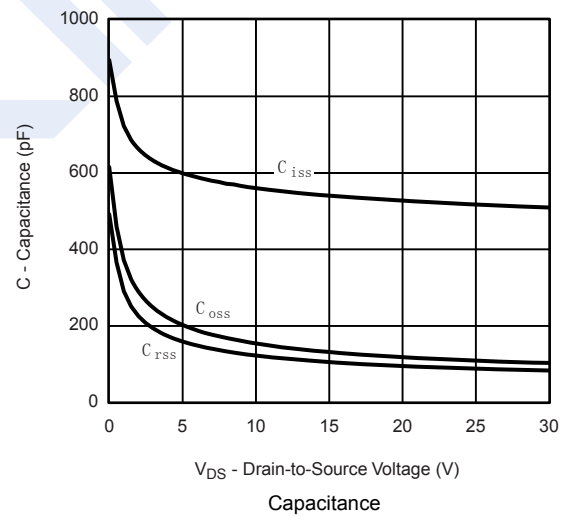
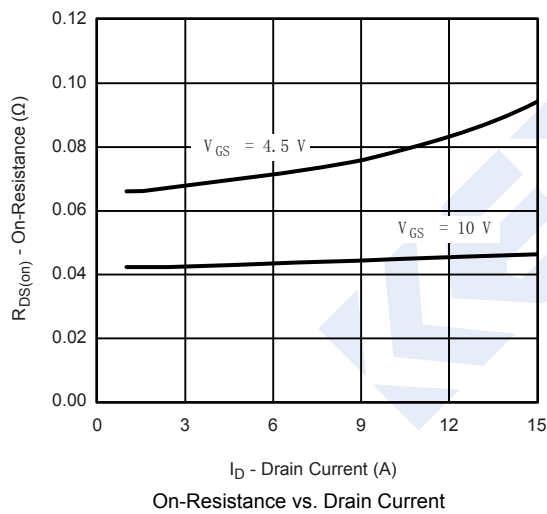
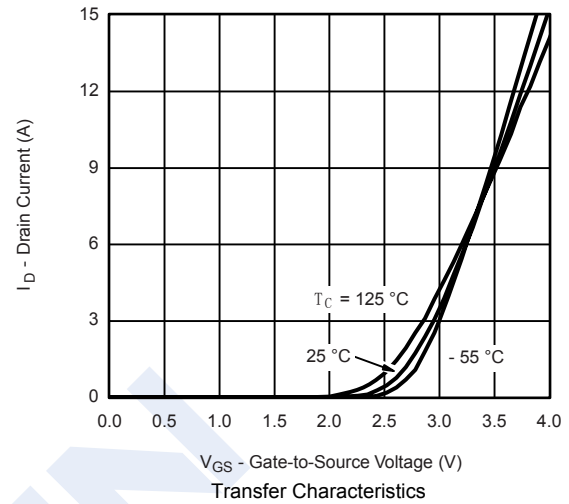
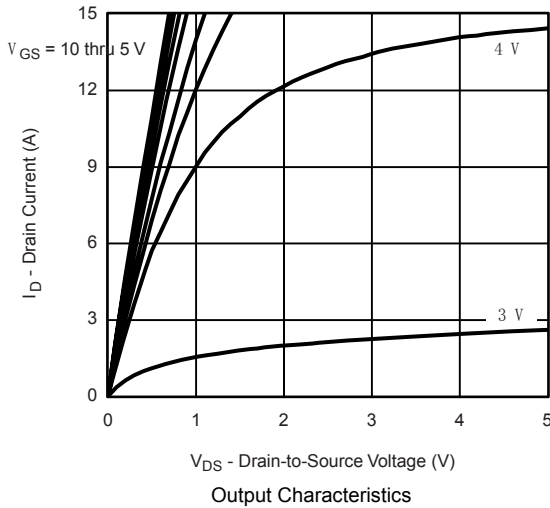
■ Marking

Marking	F3
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P-Channel MOSFET

SI2343DS (KI2343DS)

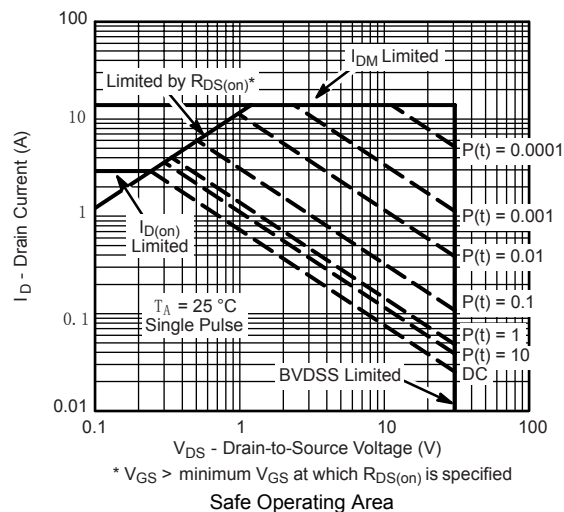
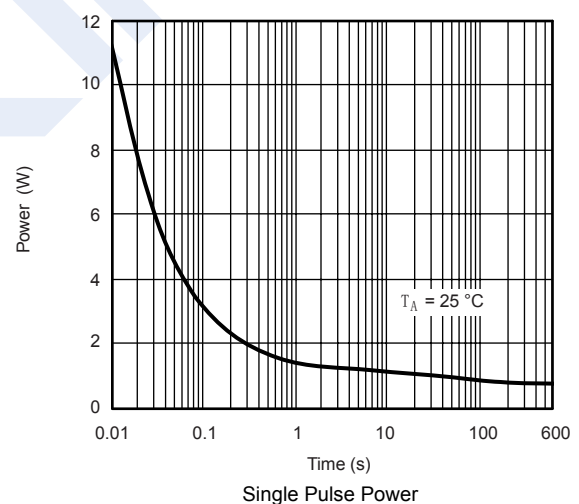
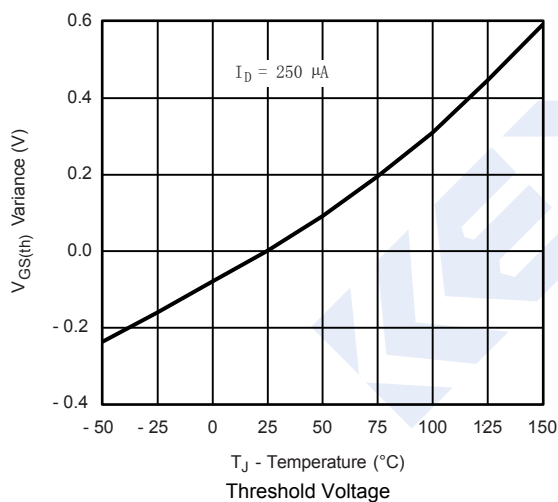
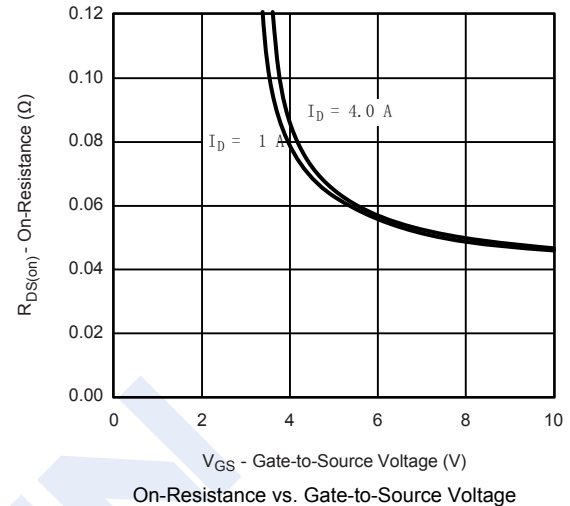
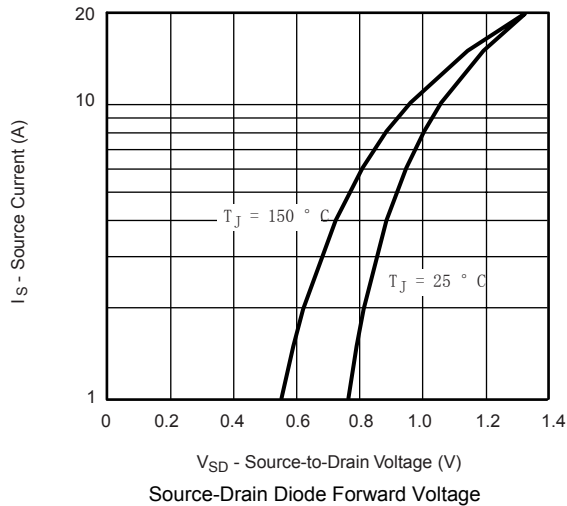
■ Typical Characteristics



P-Channel MOSFET

SI2343DS (KI2343DS)

■ Typical Characteristics



P-Channel MOSFET

SI2343DS (KI2343DS)

■ Typical Characteristics

